# 3.3 V LVTTL/LVCMOS to Differential LVPECL Translator

#### Description

The MC100LVELT20 is a 3.3 V TTL/CMOS to differential PECL translator. Because PECL (Positive ECL) levels are used, only + 3.3 V and ground are required. The small outline SOIC–8 package and the single gate of the MC100LVELT20 makes it ideal for those applications where space, performance, and low power are at a premium.

The 100 Series contains temperature compensation.

#### **Features**

- 390 ps Typical Propagation Delay
- Maximum Input Clock Frequency > 0.8 GHz Typical
- Operating Range  $V_{CC} = 3.0 \text{ V}$  to 3.6 V with GND = 0 V
- PNP TTL Input for Minimal Loading
- Q Output will Default HIGH with Input Open
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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SOIC-8 NB D SUFFIX CASE 751-07

#### **MARKING DIAGRAM**



A = Assembly Location

L = Wafer Lot
Y = Year
W = Work Week
= Pb-Free Package

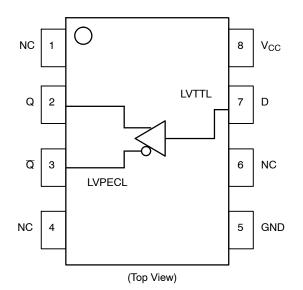
#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC100LVELT20DG	SOIC-8 NB (Pb-Free)	98 Units/Tube
MC100LVELT20DR2G	SOIC-8 NB (Pb-Free)	2500/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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<sup>\*</sup>For additional marking information, refer to Application Note <u>AND8002/D</u>.



**Table 1. PIN DESCRIPTION** 

Pin	Function
Q, Q	Differential PECL Outputs
D	LVTTL Input
V <sub>CC</sub>	Positive Supply
GND	Ground
NC	No Connect

Figure 1. 8-Lead Pinout and Logic Diagram

**Table 2. ATTRIBUTES** 

Characteristics	Value
Internal Input Pulldown Resistor	N/A
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 1.5 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB	Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	150 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

<sup>1.</sup> For additional information, see Application Note AND8003/D.

**Table 3. MAXIMUM RATINGS** 

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V <sub>CC</sub>	Power Supply	GND = 0 V		6	V
VI	Input Voltage	GND = 0 V	$V_{I} \leq V_{CC}$	6	V
I <sub>out</sub>	Output Current	Continuous Surge		50 100	mA
T <sub>A</sub>	Operating Temperature Range			-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
$\theta_{\sf JA}$	Thermal Resistance (Junction-to-Ambient)	0 Ifpm 500 Ifpm	SOIC-8 NB	190 130	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
T <sub>sol</sub>	Wave Solder (Pb-Free)			265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. LVTTL INPUT DC CHARACTERISTICS (V<sub>CC</sub> = 3.3 V, GND = 0 V, T<sub>A</sub> = -40°C to +85°C)

Symbol	Characteristic	Min	Тур	Max	Unit
I <sub>IH</sub>	Input HIGH Current (V <sub>in</sub> = 2.7 V)			20	μΑ
I <sub>IHH</sub>	Input HIGH Current MAX (V <sub>in</sub> = 6.0 V)			100	μΑ
I <sub>IL</sub>	Input LOW Current (V <sub>in</sub> = 0.5 V)			-0.6	mA
V <sub>IK</sub>	Input Clamp Voltage (I <sub>in</sub> = -18 mA)			-1.2	V
V <sub>IH</sub>	Input HIGH Voltage	2.0			V
V <sub>IL</sub>	Input LOW Voltage			0.8	V

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

Table 5. 100LVELT PECL OUTPUT DC CHARACTERISTICS (V<sub>CC</sub> = 3.3 V, GND = 0 V (Note 1))

		-40°C		25°C		85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
Icc	Negative Power Supply Current	20	25	30	22	27	32	23	28	33	mA
V <sub>OH</sub>	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V <sub>OL</sub>	Output LOW Voltage (Note 2)	1355	1480	1605	1355	1480	1605	1355	1480	1605	mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 1. Output parameters vary 1:1 with V<sub>CC</sub>.
- 2. All loading with 50  $\Omega$  to  $V_{CC}$  2.0 V.

Table 6. AC CHARACTERISTICS (V<sub>CC</sub> = 3.0 V to 3.6 V, GND = 0 V (Note 1))

		-40°C		25°C		85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f <sub>max</sub>	Maximum Input Clock Frequency (Figure 2)	600	800		600	800		600	800		MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay to Output Differential	280	350	430	300	370	450	320	400	490	ps
tskew	Device-to-Device Skew (Note 2)			250			250			250	ps
t <sub>JITTER</sub>	Random Clock Jitter (RMS) (Figure 2)		< 1	< 2		< 1	< 2		< 1	< 2	ps
t <sub>r</sub> t <sub>f</sub>	Output Rise/Fall Times Q, Q (20% - 80%)	70	100	225	80	120	225	90	140	225	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 1. Measured using a LVTTL source, 50% duty cycle clock source. All loading with 50  $\Omega$  to V<sub>CC</sub> 2.0 V.
- 2. Skew is measured between outputs under identical transitions.

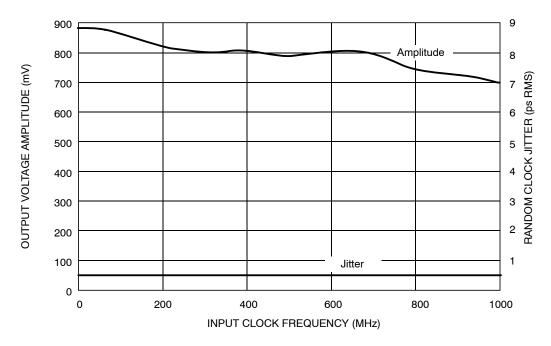


Figure 2. Output Voltage Amplitude (V<sub>OUTpp</sub>)/RMS Jitter vs. Input Clock Frequency at Ambient Temperature

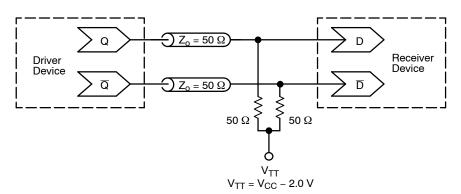


Figure 3. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices.)

#### **Resource Reference of Application Notes**

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

AN1568/D - Interfacing Between LVDS and ECL

AND8001/D - The ECL Translator Guide
AND8001/D - Odd Number Counters Design
AND8002/D - Marking and Date Codes

AND8020/D - Termination of ECL Logic Devices

AND8066/D - Interfacing with ECLinPS

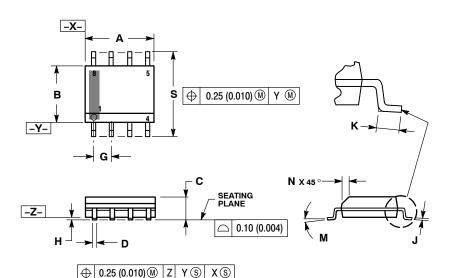
AND8090/D - AC Characteristics of ECL Devices





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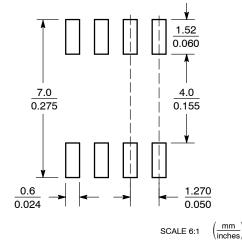
**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

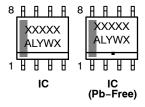
	MILLIN	IETERS	INC	HES	
DIM	MIN	MIN MAX		MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	25 0.004 0.0		
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
s	5.80	6.20	0.228	0.244	

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

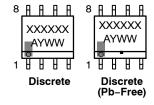
#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week W

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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#### **DATE 16 FEB 2011**

			D/ (I E TO I ED E
STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1 STYLE 6:	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1 STYLE 7:	
PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	7. DHAIN 1 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16:  PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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